Abstracts

X-Band Burnout Characteristics of GaAs MESFET's (Dec. 1982 [T-MTT])

J.J. Whalen, R.T. Kemerley and E. Rastefano. "X-Band Burnout Characteristics of GaAs MESFET's (Dec. 1982 [T-MTT])." 1982 Transactions on Microwave Theory and Techniques 30.12 (Dec. 1982 [T-MTT] (1982 Symposium Issue)): 2206-2211.

X-band µs pulse, ms pulse, and CW-burnout data have been measured for two commercially available 1- µm gate GaAs MESFET's. Values of incident pulse power required to cause burnout indicate a threshold level for pulse durations 0.2 µs or longer and for CW. The incident power threshold level for burnout is in the range 3 to 6 W for the MESFET type with a Ti/Pt/Au gate metallization and in the range 1.5 to 3 W for the MESFET type with an Al gate metallization. Many MESFET's were observed to fail during a single pulse.

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